

ABSTRACT OF THE DISCLOSURE

A semiconductor device of the present invention is arranged in such a manner that a MOS non-single-crystal silicon thin-film transistor including a non-single-crystal silicon thin film made of polycrystalline silicon, a MOS single-crystal silicon thin-film transistor including a single-crystal silicon thin film, and a metal wiring are provided on an insulating substrate. With this arrangement, (i) a semiconductor device in which a non-single-crystal silicon thin film and a single-crystal silicon thin-film device are formed and high-performance systems are integrated, (ii) a method of manufacturing the semiconductor device, and (iii) a single-crystal silicon substrate for forming the single-crystal silicon thin-film device of the semiconductor device are obtained.